

#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- ESD Protected Up To 2KV
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

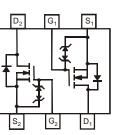
#### **Mechanical Data**

- Case: SOT-563 •
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)









TOP VIEW

TOP VIEW



### **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Char	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	20	V		
Gate-Source Voltage			V <sub>GSS</sub>	±6	V
Continuous Drain Current (Note 3)	Ι <sub>D</sub>	1.38 0.89	А		
Pulsed Drain Current (Note 4)	I <sub>DM</sub>	3	А		

### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 3)	PD	530	mW
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$ (Note 3)	R <sub>0JA</sub>	235	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

1. No purposefully added lead. Notes:

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
Device mounted on FR-4 PCB, with minimum recommended pad layout.

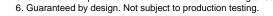
4. Repetitive rating, pulse width limited by junction temperature.

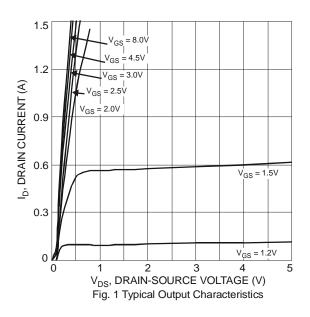


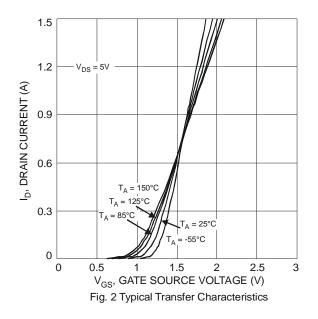
## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	100	nA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±1.0	μA	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	-	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
			0.3	0.45		$V_{GS} = 4.5V, I_D = 600mA$
			0.4	0.6		$V_{GS} = 2.5V, I_D = 500mA$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	0.5	0.75	Ω	$V_{GS} = 1.8V, I_D = 350mA$
			-	9		$V_{GS} = 1.7V, I_D = 140mA$
			-	10		$V_{GS} = 1.5V, I_D = 100mA$
Forward Transfer Admittance	Y <sub>fs</sub>	-	1.4	-	S	$V_{DS} = 10V, I_D = 400mA$
Diode Forward Voltage	V <sub>SD</sub>		0.7	1.2	V	$V_{GS} = 0V, I_{S} = 150mA$
DYNAMIC CHARACTERISTICS (Note 6)					_	
Input Capacitance	C <sub>iss</sub>	-	60.67	-	pF	
Output Capacitance	C <sub>oss</sub>	-	9.68	-	pF	$V_{DS} = 16V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	-	5.37	-	pF	1 = 1.00012
Total Gate Charge	Qg	-	736.6	-	рС	
Gate-Source Charge	Q <sub>gs</sub>	-	93.6	-	рС	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q <sub>gd</sub>	-	116.6	-	рС	$I_D = 250 \text{mA}$
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	
Turn-On Rise Time	tr	-	7.4	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t <sub>D(off)</sub>	-	26.7	-	ns	$R_{L} = 47\Omega, R_{G} = 10\Omega,$ $I_{D} = 200 \text{mA}$
Turn-Off Fall Time	t <sub>f</sub>	-	12.3	-	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.



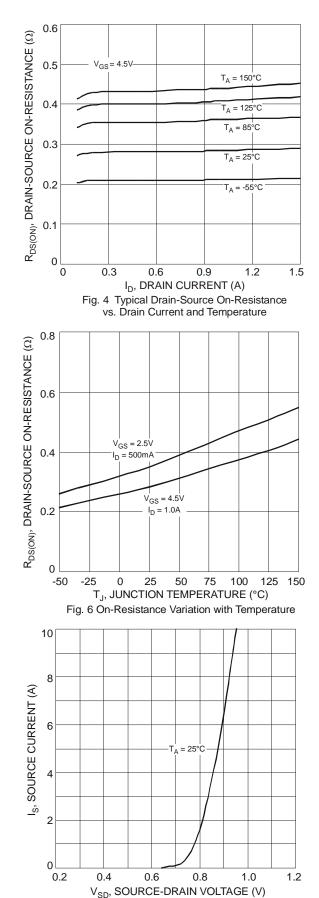






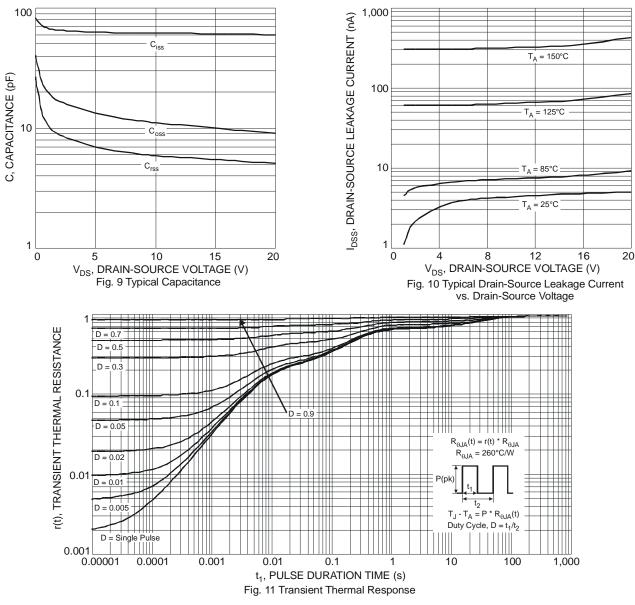
0.8  $R_{\text{DS}(\text{ON})^{\text{\prime}}}$  DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 0.7 0.6 0.5 V<sub>GS</sub> = 1.8V 0.4 V<sub>GS</sub>= 2.5V 0.3  $V_{GS} = 4.5V$ 0.2 0.1 0 0 0.3 0.6 0.9 1.2 1.5 I<sub>D</sub>, DRAIN-SOURCE CURRENT (A) Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage 1.7 R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 1.5 1.3 /<sub>GS</sub> = 2.5V = 500mA  $I_D$ V<sub>GS</sub> = 4.5V 1.1 I<sub>D</sub> = 1.0A 0.9 0.7 0.5 -25 0 25 50 75 100 125 150 -50 T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Fig. 5 On-Resistance Variation with Temperature 1.6 V<sub>GS(TH)</sub>, GATE THRESHOLD VOLTAGE (V) 1.2 0.8 I<sub>D</sub> = 250μA 0.4 0 25 50 75 100 125 150 -50 -25 0 T<sub>A</sub>, AMBIENT TEMPERATURE (°C)

Fig. 7 Gate Threshold Variation vs. Ambient Temperature





## DMG1024UV



## Ordering Information (Note 7)

Part Number	Case	Packaging
DMG1024UV-7	SOT-563	3000 / Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

### **Marking Information**

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1	NA1	,	YM	

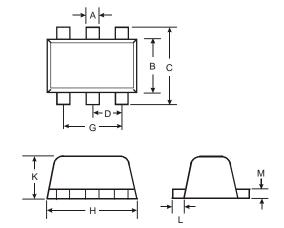
NA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)

M = Month (ex: 9 = September)

Date Code Key					-							
Year	200	9	2010		2011	20	12	2013		2014	1	2015
Code	W		Х		Y	2	7	А		В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

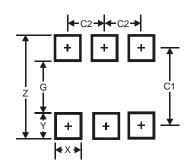


## Package Outline Dimensions



SOT-563						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
С	1.55	1.70	1.60			
D	-	-	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
Κ	0.55	0.60	0.60			
L	0.10	0.30	0.20			
Μ	0.10	0.18	0.11			
All	All Dimensions in mm					

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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